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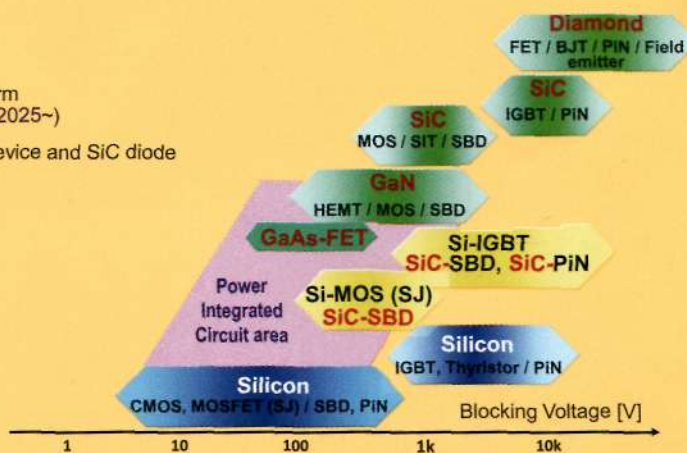
NUMBER 2

IETDAI

(ISSN 0018-9383)

SPECIAL ISSUE ON ADVANCED MODELING OF POWER DEVICES AND THEIR APPLICATIONS

-  Wide band-gap semiconductor platform
(SiC: 2010~, GaN: 2015~, Diamond: 2025~)
-  Hybrid pair platform of Si-switching device and SiC diode
(2013~2035)
-  Silicon platform
(~2030)



Advanced power semiconductor trends.

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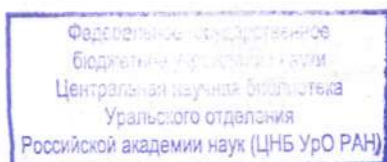
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About the Cover: The drawing on the cover represents trends of advanced power semiconductor devices shown by Ohashi and Omura in an invited review paper of this special issue. The figure summarizes different device structures with different materials for different blocking voltages, which demonstrates the wide variety of existing and future power devices usable for a wide variety of applications. All these different aspects of power devices are covered in this special issue.